

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(f))			Docket No. SETI-0002DIV	
In Re Application Of: Khan et al.				
Serial No. 10/647,714	Filing Date 8/25/2003	Examiner Unknown	Group Art Unit Unknown	
Title: METAL OXIDE SEMICONDUCTOR HETEROSTRUCTURE FIELD EFFECT TRANSISTOR				
<p>Address to: Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450</p> <p>37 CFR 1.97(b)</p> <p>1. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.</p> <p>37 CFR 1.97(c)</p> <p>2. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:</p> <p><input type="checkbox"/> the statement specified in 37 CFR 1.97(e);</p> <p>OR</p> <p><input type="checkbox"/> the fee set forth in 37 CFR 1.17(p).</p>				

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Examiner
Unknown

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Unknown

METAL OXIDE SEMICONDUCTOR HETEROSTRUCTURE FIELD EFFECT TRANSISTOR

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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Dated: **October 30, 2003**

John W. LaBatt
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INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)

ATTY DOCKET NO.
SETI-0002

SERIAL NO.
09/966,559

Khan et al.

FILING
09/27/2001

GROUP
2818

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		"Optoelectronic GaN-based Field Effect Transistors," M. S. Shur et al., SPIE, Vol. 2397, pp. 294-303, Feb. 7, 1995.
		"High Pinch-off Voltage AlGaIn-GaN Heterostructure Field Effect Transistor," M. S. Shur et al., Proceedings of ISDRS-97, pp. 377-380, Charlottesville, VA, Dec. 1997.

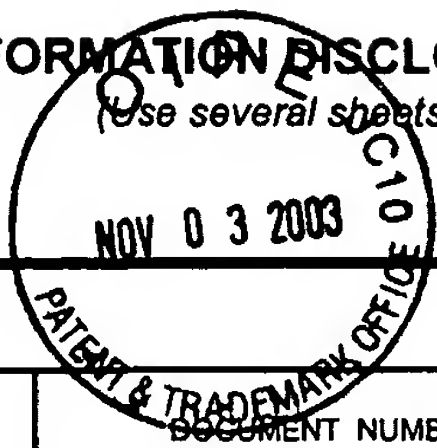
EXAMINER

DATE CONSIDERED

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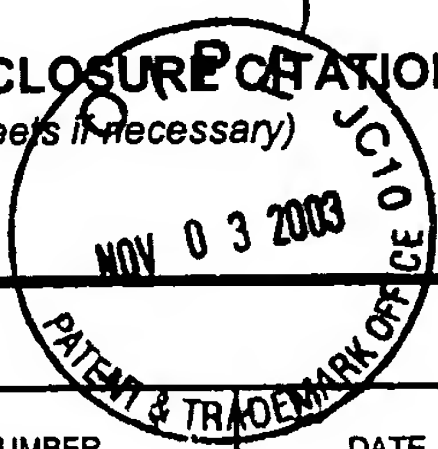
		"DC, Microwave, and High-Temperature Characteristics of GaN FET Structures," S. C. Binari et al., Inst. Phys. Conf. Ser. No. 141: Chapter 4, Presented at Int. Symp. Compound Semicond., San Diego, CA, Sept. 18-22, 1994, pp. 459-462.
		"GaN - Al _x Ga _{1-x} N Heterostructures Deposition by Low Pressure Metalorganic Chemical Vapor Deposition For Metal Insulator Semiconductor Field Effect Transistor (MISFET) Devices," M. Khan et al., Material Research Society Symposium Proceedings Vol. 281 (1993), pp.769-774.

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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

			"Low Dark Current Transparent Schottky Barrier UV Detectors," G. Simin et al., ICNS3, Montpellier, June 1999.

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INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)

SETI-006

Application Number

09/966559

Applicant(s)

Khan et al.

Filing Date

9/27/2001

Group Art Unit

2818

*EXAMINER

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

INITIAL

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Shur, M.S. and Khan, M.A., "Wide Band Gap Semiconductors. Good Results and Great Expectations," Paper presented at 23rd Int. Symp. Compound Semiconductors, St. Petersburg, Russia, 23-27 September 1996, pp. 25-31.

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